L. Number	Hits	Search Text	DB	Time stamp
1	45245	bit adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 10:33
2	707	buried adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:34
3	1	multilayer$3 adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:48
4	0	different adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:49
5	0	multiple adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:50
6	94	(buried adj bit adj line) and multiple	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 16:53
7	0	multiple adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 11:23
8	8	doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 13:07
9	6	"6054226"	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 13:07
10	1	"6054226" and (Tantalum or Ta) and (hafnium or hf)	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 14:56
11	27	"5966012"	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 14:57
13	29	((buried adj bit adj line) and doping and deep) and shallow	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:54

12	65	(buried adj bit adj line) and doping and deep	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:27
15	0	(composite adj doping) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:28
14	25	composite adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:30
16	68	deep adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:30
17	129	shallow adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:31
18	13	(deep adj doping) and (shallow adj doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:31
19	3	(bit adj line) and ((deep adj doping) and (shallow adj doping))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 17:31
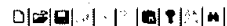
BRS:
BRS:
BRS: upside
Pending
Active
L1: (45245) bit adj line
L2: (707) buried adj bit adj line
L3: (1) multilayer$3 adj bit adj line
L4: (0) different adj doping adj bit adj line
L5: (0) multiple adj doping adj bit adj line
L6: (94) 2 and multiple
L7: (0) multiple adj doping adj bit adj line
L8: (8) doping adj bit adj line
L9: (6) "6054226"
L10: (1) 9 and (Tantalum or Ta) and (hafnium or hf
L11: (27) "5966012"
L13: (29) 12 and shallow
L12: (65) 2 and doping and deep
L15: (0) 14 and 1
L14: (25) composite adj doping
L16: (68) deep adj doping
L17: (129) shallow adj doping
L18: (13) 16 and 17
L19: (3) 1 and 18
Failed

DBs: | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Default operator: OR

Plurals
Highlight all hit terms initially

Browse   Queue   Clear

1 and 18

BRS form   ISR form   Image   Text   HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P		3	Image Do
1	☐	☐	US 20020181287 A1	20021205	10	Channel write/erase flash memory cell and its manufacturing method	365/185.29	365/185.18		Hsu, Ching-Hsiang et al.	☑	☐	☐	☐	☐	US 200201
2	☑	☐	US 20020136058 A1	20020926	10	Channel write/erase flash memory cell and its manufacturing method	365/185.18			Hsu, Ching-Hsiang et al.	☐	☐	☐	☐	☐	US 200201
3	☐	☐	US 6501685 B2	20021231	10	Channel write/erase flash memory cell and its manufacturing method	365/185.33	257/315; 257/316;		Hsu, Ching-Hsiang et al.	☑	☐	☐	☐	☐	US 650168

Hits   Details   HTML

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